



### 15 A, 1200 V, Hyperfast Diode

The RHRP15120 is a hyperfast diode with soft recovery characteristics. It has the half recovery time of ultrafast diodes and is silicon nitride passivated ionimplanted epitaxial planar construction. These devices are intended to be used as freewheeling/ clamping diodes and diodes in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

### Features

- ☑ Hyperfast Recovery  $t_{rr} = 75 \text{ ns}$  (@  $I_F = 15 \text{ A}$ )
- ☑ Max Forward Voltage,  $V_F = 3.2 \text{ V}$  (@  $T_C = 25^\circ\text{C}$ )
- ☑ 1200 V Reverse Voltage and High Reliability
- Avalanche Energy Rated
- RoHS Compliant

### Applications

- ☑ Switching Power Supplies
- ☑ Power Switching Circuits
- ☑ General Purpose

### Ordering Information

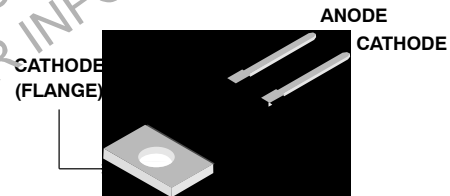
PART NUMBER	PACKAGE	BRAND
RHRP15120	TO-220AC-2L	RHR15120

NOTE: When ordering, use the entire part number.

### Packaging

JEDEC TO-220AC

### Symbol



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

	RHRP15120	UNIT
Peak Repetitive Reverse Voltage.....	1200	V
Working Peak Reverse Voltage.....	1200	V
DC Blocking Voltage.....	1200	V
Average Rectified Forward Current..... ( $T_C = 140^\circ\text{C}$ )	15	A
Repetitive Peak Surge Current..... (Square Wave, 20 kHz)	30	A
Nonrepetitive Peak Surge Current..... (Halfwave, 1 Phase, 60 Hz)	200	A
Maximum Power Dissipation.....	100	W
Avalanche Energy (See Figures 10 and 11).....	20	mJ
Operating and Storage Temperature.....	-65 to 175	$^\circ\text{C}$

**Electrical Specifications**  $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
$V_F$	$I_F = 15\text{ A}$	--		3.2	V
	$I_F = 15\text{ A}, T_C = 150^\circ\text{C}$	--		2.6	V
$I_R$	$V_R = 1200\text{ V}$	--		100	$\mu\text{A}$
	$V_R = 1200\text{ V}, T_C = 150^\circ\text{C}$	--		500	$\mu\text{A}$
$T_{rr}$	$I_F = 1\text{ A}, dI_F/dt = 100\text{ A}/\mu\text{s}$	--		65	ns
	$I_F = 15\text{ A}, dI_F/dt = 100\text{ A}/\mu\text{s}$	--		75	ns
$t_a$	$I_F = 15\text{ A}, dI_F/dt = 100\text{ A}/\mu\text{s}$	--	36	--	ns
$t_b$	$I_F = 15\text{ A}, dI_F/dt = 100\text{ A}/\mu\text{s}$	--	28	--	ns
$Q_{rr}$	$I_F = 15\text{ A}, dI_F/dt = 100\text{ A}/\mu\text{s}$	--	150	--	nC
$C_J$	$V_R = 10\text{ V}, I_F = 0\text{ A}$	--	55	--	pF
$R_{\theta JC}$		--		1.5	$^\circ\text{C}/\text{W}$

**DEFINITIONS**

$V_F$  = Instantaneous forward voltage (pw = 300  $\mu\text{s}$ , D = 2%).

$I_R$  = Instantaneous reverse current.

$t_{rr}$  = Reverse recovery time (See Figure 9), summation of  $t_a + t_b$ .

$t_a$  = Time to reach peak reverse current (See Figure 9).

$t_b$  = Time from peak  $I_{RM}$  to projected zero crossing of  $I_{RM}$  based on a straight line from peak  $I_{RM}$  through 25% of  $I_{RM}$  (See Figure 9).

$Q_{rr}$  = Reverse recovery charge.

$C_J$  = Junction capacitance.

$R_{\theta JC}$  = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

**Typical Performance Curves**

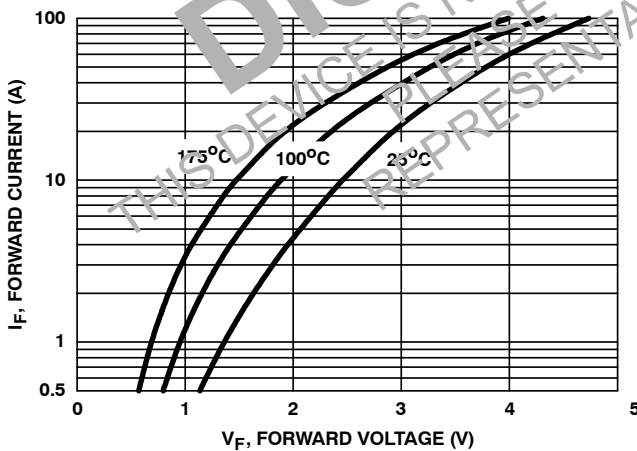


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

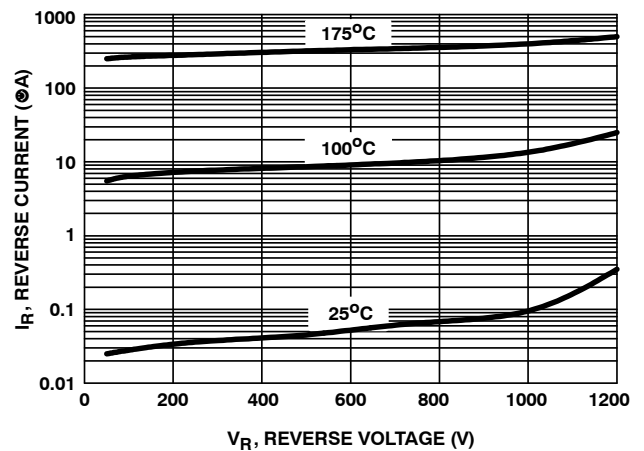


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

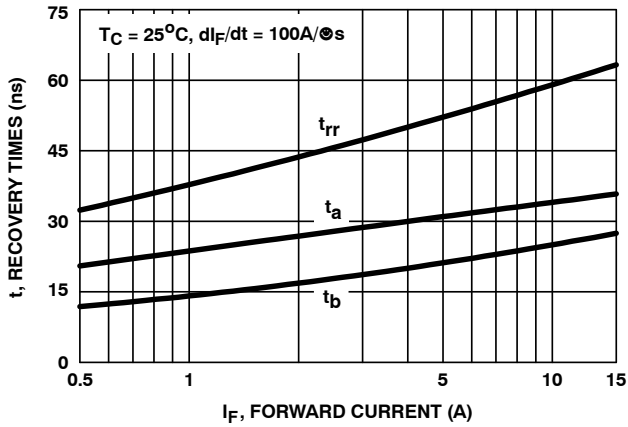


FIGURE 3.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

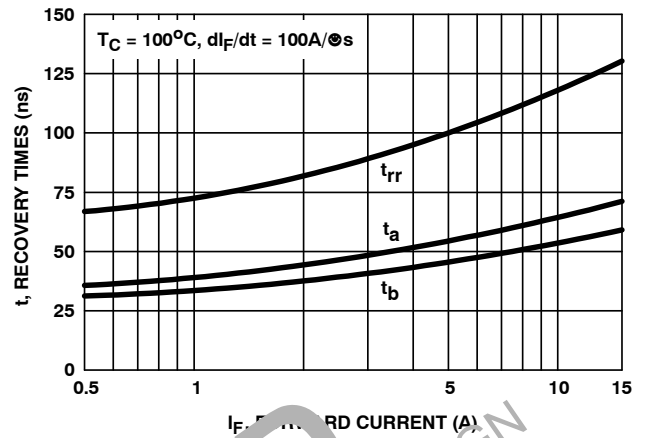


FIGURE 4.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

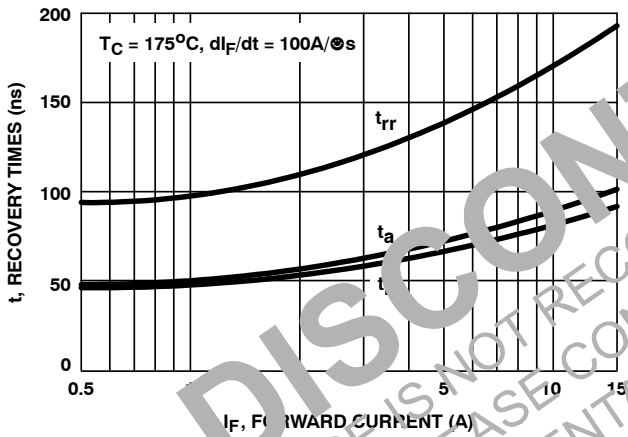


FIGURE 5.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

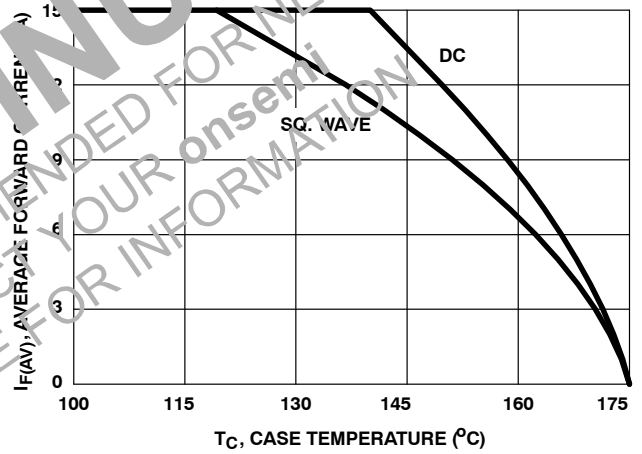


FIGURE 6. CURRENT DERATING CURVE

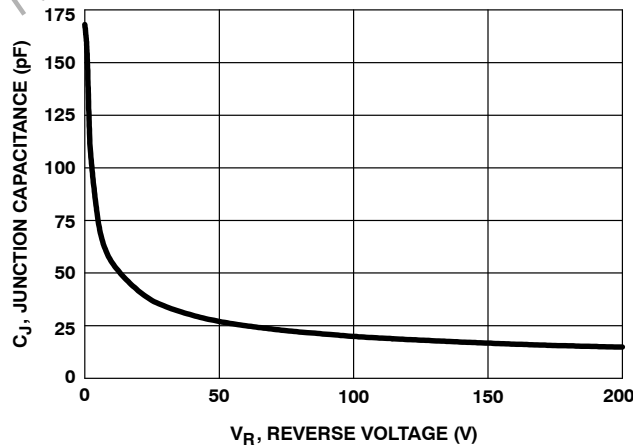


FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

**Test Circuits and Waveforms**

$V_{GE}$  AMPLITUDE AND  
 $R_G$  CONTROL  $di_F/dt$   
 $t_1$  AND  $t_2$  CONTROL  $I_F$

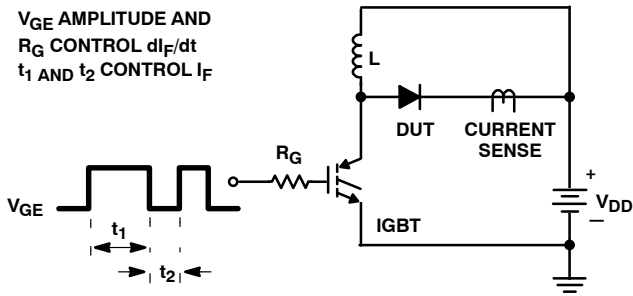


FIGURE 8.  $t_{rr}$  TEST CIRCUIT

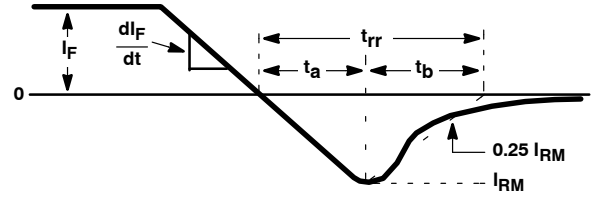


FIGURE 9.  $t_{rr}$  WAVEFORMS AND DEFINITIONS

$I_{MAX} = 1A$   
 $L = 40mH$   
 $R < 0.1\Omega$   
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)}/(V_{R(AVL)} - V_D)]$   
 $Q_1 = IGBT (BV_{CES} > DUT V_{R(AVL)})$

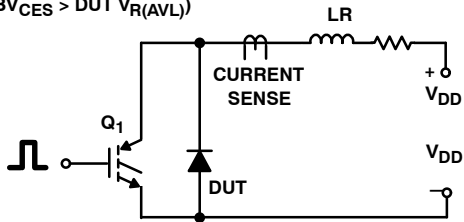


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

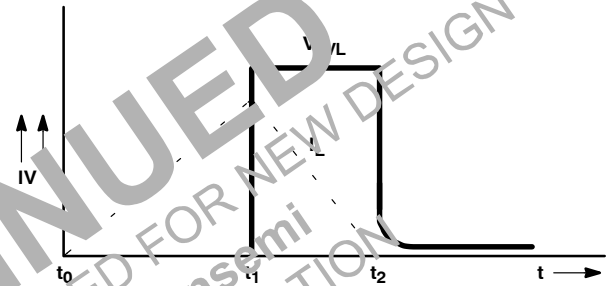



FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

DISCONTINUED

THIS DEVICE IS NOT RECOMMENDED FOR NEW DESIGN  
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